

Title (en)

Method for aligning semiconductor die to interconnect metal on flex substrate

Title (de)

Methode zur Ausrichtung eines Halbleiterchips zu einem Verbindungsmetall auf einem flexiblen Substrat

Title (fr)

Méthode pour l'alignement d'une puce semi-conductrice avec un métal d'interconnexion sur un substrat flexible

Publication

EP 1111662 A2 20010627 (EN)

Application

EP 00311553 A 20001221

Priority

US 46974999 A 19991222

Abstract (en)

A method and process sequence for accurately aligning (14) die (108) to interconnect metal (112) on flex substrate (100) such as polyimide flex is described. A mask (102) for via formation is first patterned (12) in a metal layer on the bottom surface of the flex substrate (100). Die attach means (104) such as die attach adhesive is then applied (13) to the top side of flex substrate (100). The bond pads (106) on die are locally, adaptively aligned (14) to the patterned metal via mask (102) on the flex (100) with high accuracy. Vias (110) down to the die bond pads (106) are then created (15) by either plasma etching or excimer laser ablation through the existing aligned metal mask (102) on the flex substrate (100), and interconnect metal (112) is then deposited (16), patterned and etched (17). As a result of this process, the flex metal interconnect artwork does not have to be customized for each die misplacement using "adaptive lithography". Lower cost commercially available lithography equipment can be used for processing, reducing capital equipment and processing cost. The method is compatible with the projected designs of the next generation die which will have bond pads on the order of 40 mu m in size. <IMAGE>

IPC 1-7

H01L 21/00

IPC 8 full level

H01L 21/00 (2006.01); **H05K 3/40** (2006.01); **H01L 21/60** (2006.01); **H01L 21/68** (2006.01); **H01L 23/00** (2006.01); **H01L 23/12** (2006.01); **H01L 23/538** (2006.01); **H05K 3/00** (2006.01)

CPC (source: EP US)

H01L 23/5389 (2013.01 - EP US); **H01L 24/19** (2013.01 - EP US); **H01L 24/76** (2013.01 - EP US); **H01L 24/82** (2013.01 - EP US); **H01L 2223/54426** (2013.01 - EP US); **H01L 2224/04105** (2013.01 - EP US); **H01L 2224/32225** (2013.01 - EP US); **H01L 2224/8314** (2013.01 - EP US); **H01L 2224/83192** (2013.01 - EP US); **H01L 2224/92144** (2013.01 - EP US); **H01L 2924/01004** (2013.01 - EP US); **H01L 2924/01005** (2013.01 - EP US); **H01L 2924/01006** (2013.01 - EP US); **H01L 2924/01013** (2013.01 - EP US); **H01L 2924/01018** (2013.01 - EP US); **H01L 2924/01027** (2013.01 - EP US); **H01L 2924/01029** (2013.01 - EP US); **H01L 2924/01033** (2013.01 - EP US); **H01L 2924/01039** (2013.01 - EP US); **H01L 2924/01074** (2013.01 - EP US); **H01L 2924/01075** (2013.01 - EP US); **H01L 2924/01078** (2013.01 - EP US); **H01L 2924/01082** (2013.01 - EP US); **H01L 2924/01087** (2013.01 - EP US); **H01L 2924/12042** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/1423** (2013.01 - EP US); **Y10T 29/49131** (2015.01 - EP US)

C-Set (source: EP US)

H01L 2924/12042 + H01L 2924/00

Citation (applicant)

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Designated contracting state (EPC)

DE FR

DOCDB simple family (publication)

EP 1111662 A2 20010627; **EP 1111662 A3 20031001**; **EP 1111662 B1 20121212**; CN 1199250 C 20050427; CN 1301039 A 20010627; JP 2001250888 A 20010914; JP 4931277 B2 20120516; TW 490716 B 20020611; US 2002197767 A1 20021226; US 6475877 B1 20021105; US 6790703 B2 20040914

DOCDB simple family (application)

EP 00311553 A 20001221; CN 00136449 A 20001222; JP 2000388006 A 20001221; TW 89126381 A 20001211; US 19929602 A 20020722; US 46974999 A 19991222